

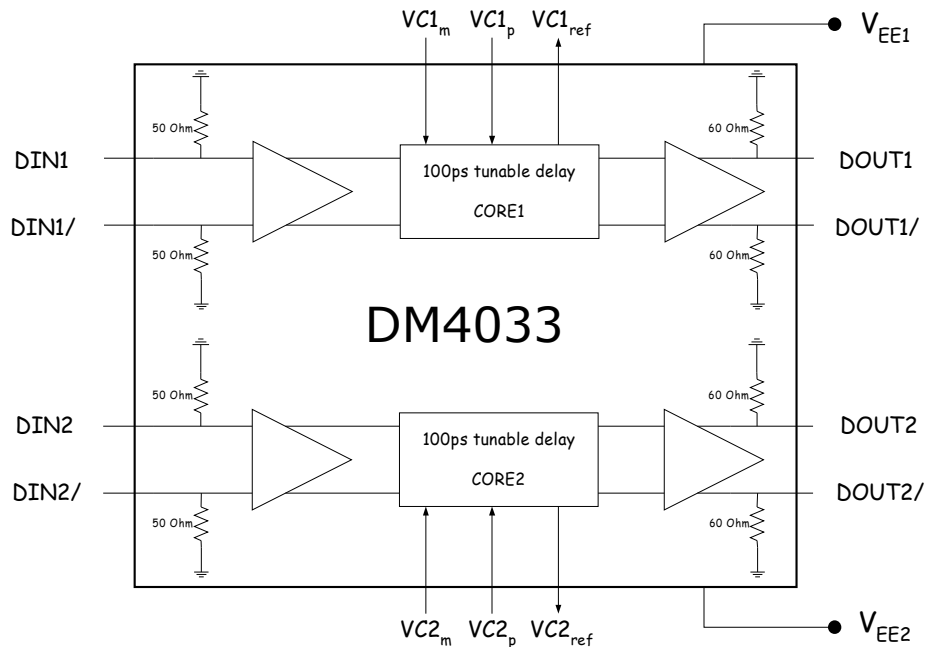
Description

The DM4033 is a dual-independent ultra-wideband phase delay fabricated using 1-um HBT GaAs technology and is based on ECL topology to guarantee high-speed operation. The high output voltage, excellent rise and fall time, and the high eye diagram quality at data rates to 12.5 Gb/s makes the DM4033 suitable for timing adjustment in data and clock distribution at very high speed. Complex digital applications benefit from the DM4033, including clock data recovery, edge detectors, NRZ-to-RZ converters, MUX/DEMUX, and data restoration. The device features a dual delay element that provides up to 100-ps delay. Delay control can be either differential (using both VCp and VCm) or single-ended (VCm is the active control pad while VCp is shorted to VCref). The control voltage range for the delay input is from -2.2 V to -3.0 V whether the control is single-ended or differential. The device can delay NRZ streams with data rates to 12.5 Gb/s or a clock signal up to 10.7 GHz. Both inputs and outputs are DC-coupled. At the input side, internal 50-ohm resistors avoid the need for external impedance matching terminations. The DM4033 uses SCFL I/O levels and is designed so to allow for either single ended or differential data input.

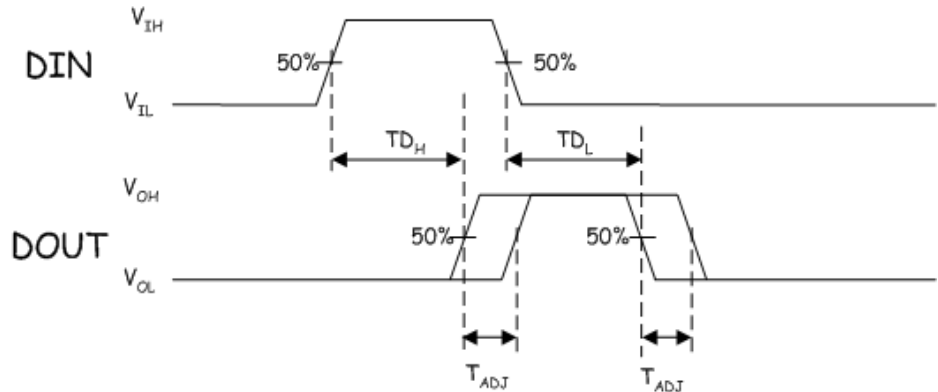
Features

- Ultra wideband: Up to 12.5 Gb/s NRZ
- Dual independent cores on a single die
- Delay adjustment to 100 ps
- 900 mVpp single-ended output
- Jitter RMS: <1.5 ps
- Output rise time (20% – 80 %): <21 ps
- Output fall time (20% – 80 %): <18 ps
- 50-ohm matched DC-coupled inputs and outputs
- Differential or single ended I/O
- Power consumption: 1.6 W (each core)

Device Diagram



Timing Diagram



Absolute Maximum Ratings

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational section of this document is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Symbol	Parameters/conditions	Min.	Max.	Units
V_{EE}	Power supply voltage	-5.5	0	V
V_{IH}	Input voltage level, high level	-1.5	1.5	V
V_{IL}	Input voltage level, low level	-1.5	1.5	V
VC	Delay control voltage	-5.0	0	V
T_A	Operating temperature range – die	-15	125	°C
T_{STG}	Storage temperature	-65	150	°C

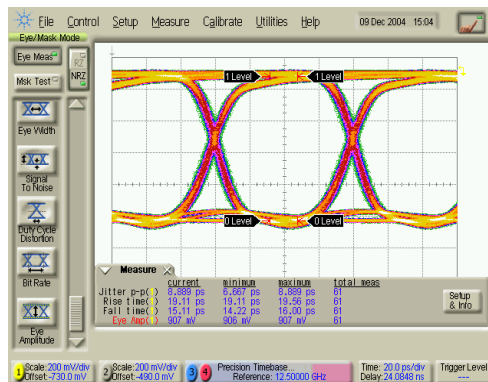
Recommended Operating Conditions

Symbol	Parameters/conditions	Min.	Typ.	Max	Units
T_A	Operating temperature range – die	0		85	°C
V_{EE}	Power supply voltage		-5		V
VC	Delay control voltage	-3.0	-2.6	-2.2	V
V_{IH}	Input voltage level, high level (single ended)		0.0		V
V_{IL}	Input voltage level, low level (single ended)		-0.9		V
V_{INDC}	DC input voltage (with DC-coupled input)		-0.4 5		V

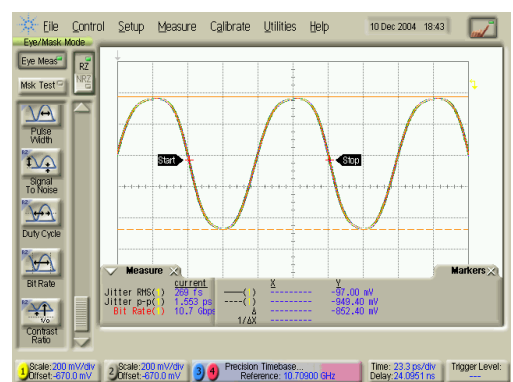
Electrical Characteristics

1. Electrical characteristics at ambient temperature.
2. In case of single-ended input the unused pin has to be tied to VINDC.
3. In case of single-ended output the unused one has to be terminated via DC block plus 50 ohms to ground.
4. Refer to timing diagram.
5. On a 10.7 Gb/s PRBS pattern.

Symbol	Parameters	Min	Typ	Max	Units
V_{EE}	Power supply voltage	-4.5	-5.00	-5.25	V
V_{IH}	Input voltage level, high level (single ended)		0.0		V
V_{IL}	Input voltage level, low level (single ended)		-0.9		V
V_{INDC}	DC input voltage (with DC-coupled input) ⁽²⁾		-0.45		V
V_{OUT}	Data output voltage amplitude ⁽³⁾	0.8	0.9	1.0	V
T_R	Output rise time (20% – 80%)		20		ps
T_F	Output fall time (20% – 80%)		17		ps
TD_H	Output delay low-high transition ⁽⁴⁾		250		ps
TD_L	Output delay high-low transition ⁽⁴⁾		250		ps
T_{ADJ}	Output phase delay adjustment ⁽⁴⁾		100		ps
S_{11}	Input return loss (up to 15 GHz)		24		dB
S_{22}	Output return loss (up to 15 GHz)		8		dB
F_{MAX}	Maximum clock frequency		10.7		GHz
J_{p-p}	Peak-to-peak jitter ⁽⁵⁾		9		ps
J_{rms}	RMS jitter ⁽⁵⁾		1.5		ps
I_{EE}	Power supply current		642		mA
P_D	Power dissipation		3.21		W

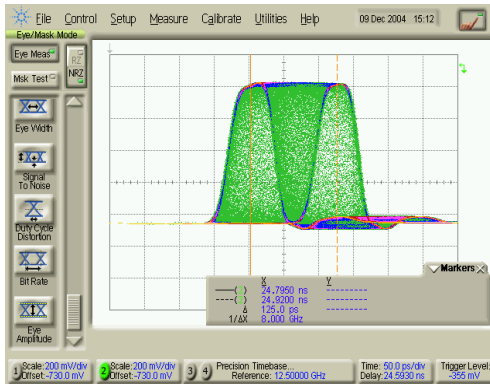
Eye Diagram Performance


Die measurement
 Vee: -5.0 V
 Input data rate: 12.5 GHz
 Differential data input: 0/-900 mVpp
 Control voltage: $V_{Cp} = V_{Cref}$,
 $V_{Cm} = -2.6$ V

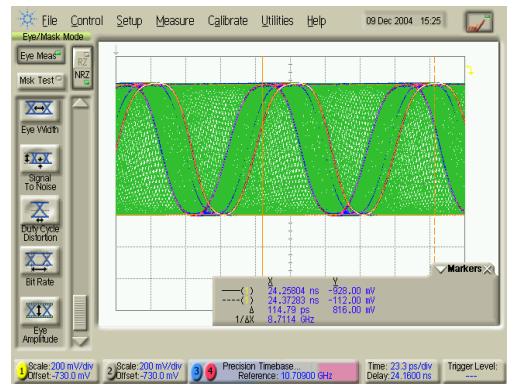


Die measurement
 Vee: -5.0 V
 Input CLK frequency: 10.7 GHz
 Single-ended CLK input: +/-450 mVpp
 Control voltage: $V_{Cp} = V_{Cref}$,
 $V_{Cm} = -2.2$ to -3.0 V (accumulating)

Eye Diagram Performance (cont.)

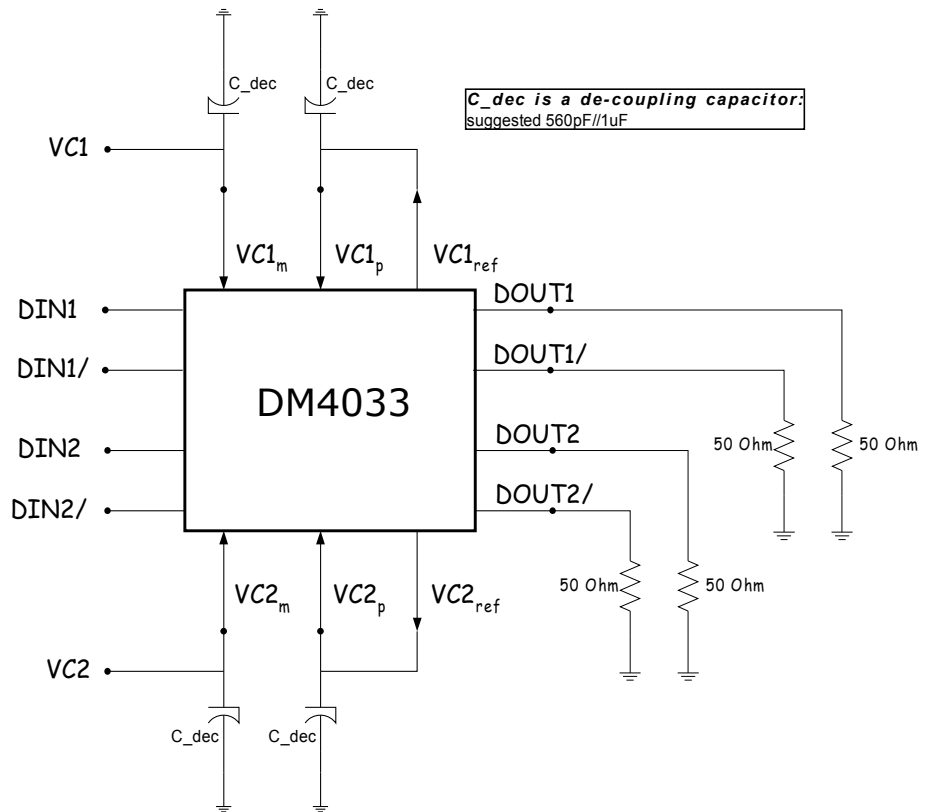


Die measurement
Vee: -5.0 V
Input data rate: 12.5 GHz
Differential data input: 0/-900 mVpp
Control voltage: $VC_p = VC_{ref}$,
 $VC_m = -2.2$ to -3.0 V (accumulating)



Die measurement
Vee: -5.0 V
Input CLK frequency: 10.7 GHz
Single-ended CLK input: +/-450 mVpp
Control voltage: $VC_p = VC_{ref}$,
 $VC_m = -2.2$ to -3.0 V (accumulating)

Recommended Operational Setup



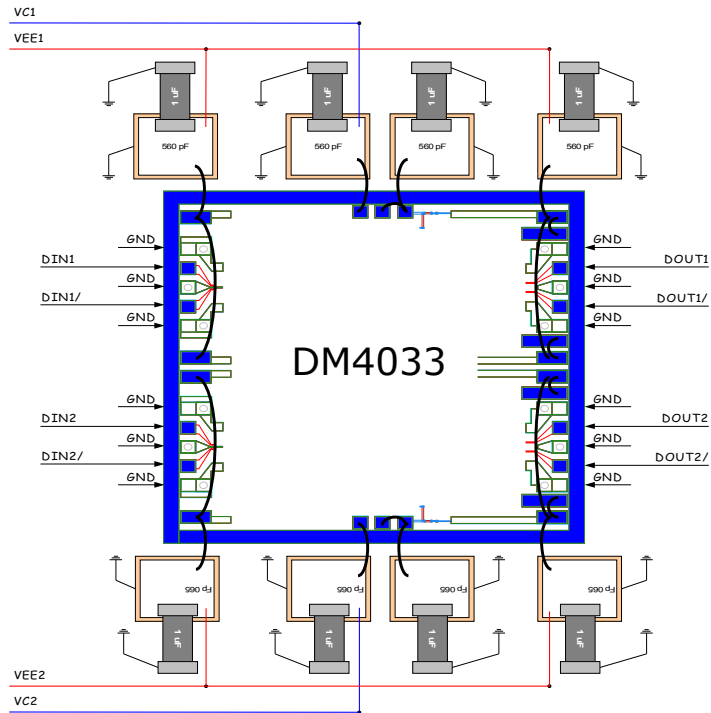
Recommended Chip Mounting

Chip size:
2650 μm \pm 10 μm
x 2650 μm \pm 10 μm

Chip thickness:
104 μm \pm 3 μm

Pad size: 100 μm
x 100 μm

RF pad pitch: 150 μm



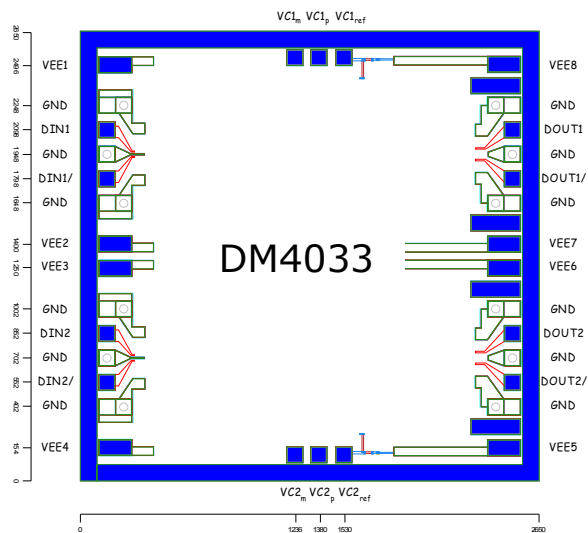
Pad Positions and Chip Dimensions

Chip size:
2650 μm \pm 10 μm
x 2650 μm \pm 10 μm

Chip thickness:
104 μm \pm 3 μm

Pad size: 100 μm
x 100 μm

RF pad pitch: 150 μm



Disclaimer

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**Application
Information**
CAUTION: THIS IS AN ESD SENSITIVE DEVICE

Chip carrier material should be selected to have GaAs compatible thermal coefficient of expansion and high thermal conductivity such as copper molybdenum or copper tungsten. The chip carrier should be machined, finished flat, plated with gold over nickel and should be capable of withstanding 325°C for 15 minutes.

Die attachment for power devices should utilize Gold/Tin (80/20) eutectic alloy solder and should avoid hydrogen environment for HBT devices. Note that the backside of the chip is gold plated and it is connected to RF and DC Ground.

These GaAs devices should be handled with care and stored in dry nitrogen environment to prevent contamination of bonding surfaces. These are ESD sensitive devices and should be handled with appropriate precaution including the use of wrist-grounding straps. All die attach and wire/ribbon bond equipment must be well grounded to prevent static discharges through the device.

Recommended wire bonding: for Signal input / output connections, use either 3 mils wide and 0.5 mil thick gold ribbon or a pair of 1mil diameter wires with lengths as short as practical allowing for appropriate stress relief (typically 400 +/- 100 um long). For all other connections, a single 1 mil dia wire of appropriate minimum length may be used.

**Product
Status
Definitions**

Datasheet Identification	Product Status	Definition
Advanced Information	Formative or or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. DIGIMIMIC reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. DIGIMIMIC reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not in Production	This datasheet contains specifications on a product that has been discontinued by DIGIMIMIC. The datasheet is printed for reference information only.